

CentralTM
Semiconductor Corp.

DESCRIPTION:
The CENTRAL SEMICONDUCTOR CMPTA27 type is a Silicon NPN Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

Marking Code is FG.

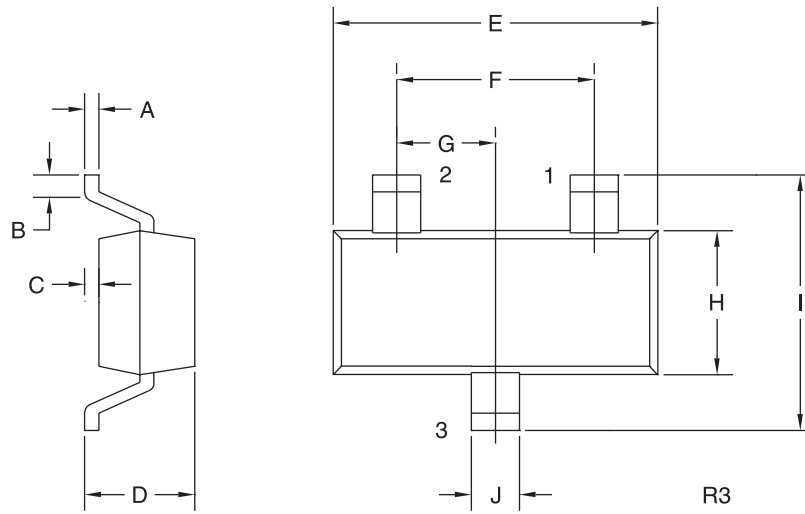
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CES}	60	V
Emitter-Base Voltage	V _{EBO}	10	V
Collector Current	I _C	500	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CES}	V _{CE} =50V		500	nA
I _{CBO}	V _{CB} =50V		100	nA
I _{EBO}	V _{BE} =10V		100	nA
BV _{CES}	I _C =100μA	60		V
BV _{CBO}	I _C =100μA	60		V
V _{CE(SAT)}	I _C =100mA, I _B =0.1mA		1.5	V
V _{BE(ON)}	V _{CE} =5.0V, I _C =100mA		2.0	V
h _{FE}	V _{CE} =5.0V, I _C =10mA	10,000		
h _{FE}	V _{CE} =5.0V, I _C =100mA	10,000		
f _T	V _{CE} =5.0V, I _C =10mA, f=100MHz	125		MHz

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

MARKING CODE: FG

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)